NL17SH125

Non-Inverting 3-State Buffer

The NL17SH125 MiniGate™ is an advanced high−speed CMOS non−inverting buffer in ultra−small footprint.

The NL17SH125 requires the 3−state control input ($\overline{OE}$) to be set High to place the output in the high impedance state.

The NL17SH125 input structures provide protection when voltages up to 7.0 V are applied, regardless of the supply voltage.

Features

- High Speed: t_{PD} = 3.8 ns (Typ) at V_{CC} = 5.0 V
- Low Power Dissipation: I_{CC} = 1.0 μA (Max) at T_A = 25°C
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- These are Pb−Free and Halide−Free Devices

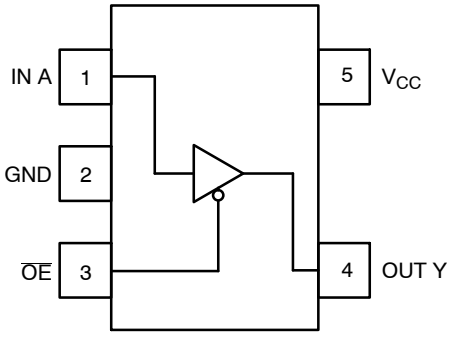

Figure 1. Pinout (Top View)

Figure 2. Logic Symbol

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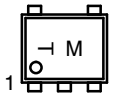
http://onsemi.com

MARKING DIAGRAM

SOT−953
CASE 527AE



T = Specific Device Code (Rotated 90°)
M = Month Code

PIN ASSIGNMENT	
1	IN A
2	GND
3	$\overline{OE}$
4	OUT Y
5	V_{CC}

FUNCTION TABLE

Input A	Input $\overline{OE}$	Output Y
L	L	L
H	L	H
X	H	Z

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_{IN}	DC Input Voltage		−0.5 to +7.0	V
V_{OUT}	DC Output Voltage		−0.5 to V_{CC} + 0.5	V
I_{IK}	DC Input Diode Current	V_{IN} < GND	−20	mA
I_{OK}	DC Output Diode Current	V_{OUT} < GND, V_{OUT} > V_{CC}	±20	mA
I_{OUT}	DC Output Source/Sink Current		±12.5	mA
I_{CC}	DC Supply Current per Supply Pin		±25	mA
I_{GND}	DC Ground Current per Ground Pin		±25	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature Under Bias		+150	°C
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V−0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>3000 >150 N/A	V
$I_{LATCHUP}$	Latchup Performance	Above V_{CC} and Below GND at 125°C (Note 5)	±100	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 2−ounce copper trace with no air flow.
2. Tested to EIA/JESD22−A114−A.
3. Tested to EIA/JESD22−A115−A.
4. Tested to JESD22−C101−A.
5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		1.65	5.5	V
V_{IN}	Digital Input Voltage		0.0	5.5	V
V_{OUT}	Output Voltage		0.0	V_{CC}	V
T_A	Operating Temperature Range		−55	+125	°C
$\Delta t / \Delta V$	Input Transition Rise or Fail Rate	V_{CC} = 3.3 V ± 0.3 V V_{CC} = 5.0 V ± 0.5 V	0 0	100 20	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} (V)	T_A = 25°C			$T_A \leq$ 85°C		−55°C to 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V_{IH}	High−Level Input Voltage		1.65 to 2.0	0.75 x V_{CC}			0.75 x V_{CC}				V
			2.3 to 5.5	0.70 x V_{CC}			0.70 x V_{CC}				
V_{IL}	Low−Level Input Voltage		1.65 to 2.0			0.25 x V_{CC}		0.25 x V_{CC}		0.25 x V_{CC}	V
			2.3 to 5.5			0.30 x V_{CC}		0.30 x V_{CC}		0.30 x V_{CC}	
V_{OH}	High−Level Output Voltage	V_{IN} = V_{IH} or V_{IL} I_{OH} = −50 μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		V_{IN} = V_{IH} or V_{IL} I_{OH} = −4 mA I_{OH} = −8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V_{OL}	Low−Level Output Voltage	V_{IN} = V_{IH} or V_{IL} I_{OL} = 50 μA	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		V_{IN} = V_{IH} or V_{IL} I_{OL} = 4 mA I_{OL} = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I_{IN}	Input Leakage Current	0 ≤ V_{IN} ≤ 5.5 V	0 to 5.5			±0.1		±1.0		±1.0	μA
I_{CC}	Quiescent Supply Current	0 ≤ V_{IN} ≤ V_{CC}	5.5			1.0		10		40	μA
I_{OZ}	3−State Leakage Current	V_{IN} = V_{IH} or V_{IL} V_{OUT} = V_{CC} or GND	0.0			±0.25		±2.5		±2.5	μA

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f$ = 3.0 ns)

Symbol	Parameter	V_{CC} (V)	Test Conditions	T_A = 25°C			$T_A \leq$ 85°C		−55°C to 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay, A to Y	3.0 to 3.6	C_L = 15 pF C_L = 50 pF		5.6 8.1	8.0 11.5	1.0 1.0	9.5 13.0		12.0 16.0	ns
		4.5 to 5.5	C_L = 15 pF C_L = 50 pF		3.8 5.3	5.5 7.5	1.0 1.0	6.5 8.5		8.5 10.5	
t_{PZL}, t_{PZH}	Output Enable Time, $\overline{OE}$ to Y	3.0 to 3.6	C_L = 15 pF C_L = 50 pF		5.4 7.9	8.0 11.5	1.0 1.0	9.5 13.0		11.5 15.0	ns
		4.5 to 5.5	C_L = 15 pF C_L = 50 pF		3.6 5.1	5.1 7.1	1.0 1.0	6.0 8.0		7.5 9.5	
t_{PLZ}, t_{PHZ}	Output Enable Time, $\overline{OE}$ to Y	3.0 to 3.6	C_L = 15 pF C_L = 50 pF		6.5 8.0	9.7 13.2	1.0 1.0	11.5 15.0		14.5 18.5	ns
		4.5 to 5.5	C_L = 15 pF C_L = 50 pF		4.8 7.0	6.8 8.8	1.0 1.0	8.0 10		10.0 12.0	
C_{IN}	Input Capacitance				5.5	10		10		10	pF
C_{PD}	Power Dissipation Capacitance (Note 6)	5.0			11						pF

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

ORDERING INFORMATION

Device	Package	Shipping†
NL17SH125P5T5G	SOT−953 (Pb−Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

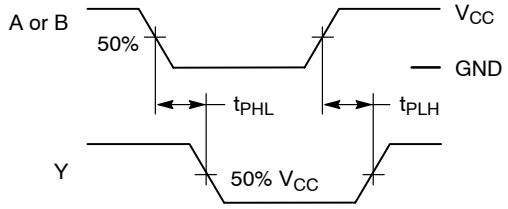


Figure 3. Switching Waveform

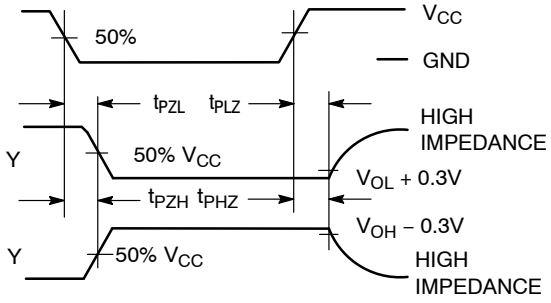
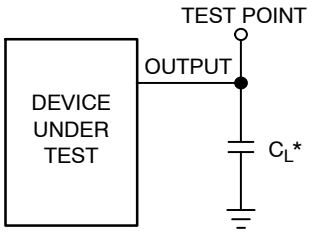
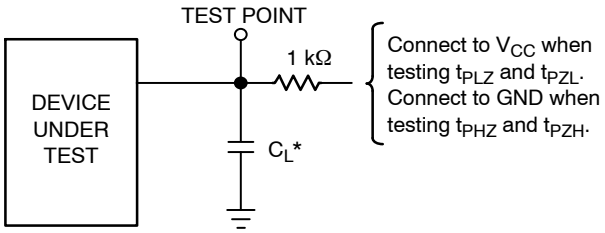


Figure 4.



*Includes all probe and jig capacitance.

Figure 5. Test Circuit



*Includes all probe and jig capacitance.

Figure 6. Test Circuit

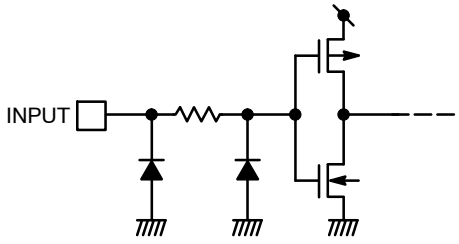
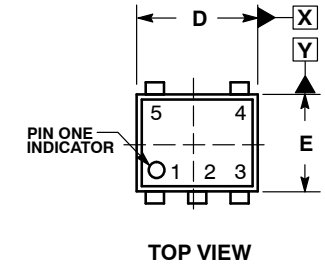


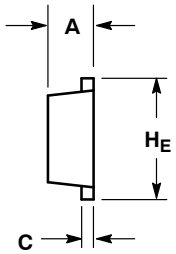
Figure 7. Input Equivalent Circuit

PACKAGE DIMENSIONS

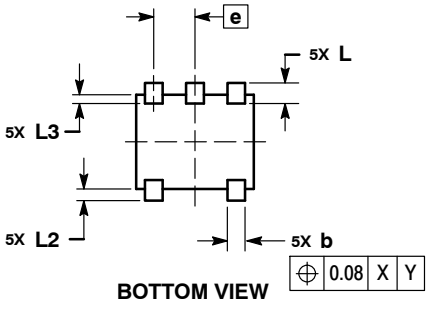
SOT−953
CASE 527AE
ISSUE E



TOP VIEW



SIDE VIEW

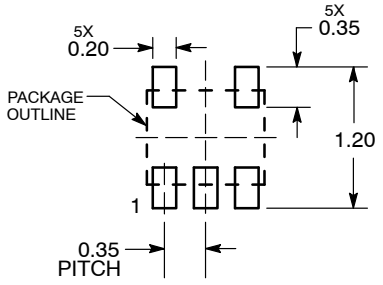


BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.34	0.37	0.40
b	0.10	0.15	0.20
C	0.07	0.12	0.17
D	0.95	1.00	1.05
E	0.75	0.80	0.85
e	0.35 BSC		
H_E	0.95	1.00	1.05
L	0.175 REF		
L2	0.05	0.10	0.15
L3	---	---	0.15

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

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